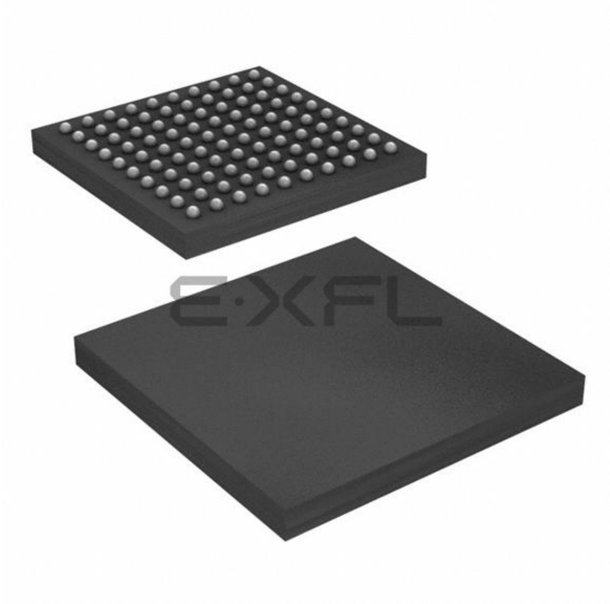

What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	e200z4
Core Size	32-Bit Single-Core
Speed	120MHz
Connectivity	CANbus, Ethernet, FlexRay, I²C, LINbus, SPI
Peripherals	DMA, I²S, POR, WDT
Number of I/O	-
Program Memory Size	1.5MB (1.5M x 8)
Program Memory Type	FLASH
EEPROM Size	64K x 8
RAM Size	192K x 8
Voltage - Supply (Vcc/Vdd)	3.15V ~ 5.5V
Data Converters	A/D 36x10b, 16x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	100-LFBGA
Supplier Device Package	100-MAPBGA (11x11)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/spc5744bk1avmh2r

Table 1. MPC5746C Family Comparison1 (continued)

Feature	MPC5745B	MPC5744B	MPC5746B	MPC5744C	MPC5745C	MPC5746C
I^2C	4	4	4	4		
SAI/I^2S	3	3	3	3		
FXOSC	8 - 40 MHz					
SXOSC	32 KHz					
FIRC	16 MHz					
SIRC	128 KHz					
FMPLL	1					
Low Power Unit (LPU)	Yes					
FlexRay 2.1 (dual channel)	Yes, 128 MB	Yes, 128 MB	Yes, 128 MB	Yes, 128 MB		
Ethernet (RMII, MII + 1588, Muti queue AVB support)	1	1	1	1		
CRC	1					
MEMU	2					
STCU2	1					
HSM-v2 (security)	Optional					
Censorship	Yes					
FCCU	1					
Safety level	Specific functions ASIL-B certifiable					
User MBIST	Yes					
I/O Retention in Standby	Yes					
GPIO[6]	Up to 264 GPI and up to 246 GPIO					
Debug	JTAGC, cJTAG					
Nexus	Z4 N3+ (Only available on 324BGA (development only)) Z2 N3+ (Only available on 324BGA (development only))					
Packages	176 LQFP-EP 256 BGA 100 BGA	176 LQFP-EP 256 BGA 100 BGA	176 LQFP-EP 256 BGA 100 BGA	176 LQFP-EP 256 BGA 100 BGA	176 LQFP-EP 256 BGA 100 BGA	176 LQFP-EP 256 BGA, 324 BGA (development only) 100 BGA

1. Feature set dependent on selected peripheral multiplexing, table shows example. Peripheral availability is package dependent.
2. Based on 125°C ambient operating temperature and subject to full device characterization.
3. Contact NXP representative for part number
4. Additional SWT included when HSM option selected
5. See device datasheet and reference manual for information on to timer channel configuration and functions.
6. Estimated I/O count for largest proposed packages based on multiplexing with peripherals.

Table 4. MPC5746C Family Comparison - RAM Memory Map (continued)

Start Address	End Address	Allocated size	Description	MPC5744	MPC5745	MPC5746
0x40030000	0x4003FFFF	64 KB	SRAM4	not available	available	available
0x40040000	0x4004FFFF	64 KB	SRAM5	not available	not available	available
0x40050000	0x4005FFFF	64 KB	SRAM6	not available	not available	available
0x40060000	0x4006FFFF	64 KB	SRAM7	not available	not available	optional
0x40070000	0x4007FFFF	64 KB	SRAM8	not available	not available	optional

3 Ordering parts

3.1 Determining valid orderable parts

To determine the orderable part numbers for this device, go to www.nxp.com and perform a part number search for the following device number: MPC5746C.

4.2 Recommended operating conditions

The following table describes the operating conditions for the device, and for which all specifications in the data sheet are valid, except where explicitly noted. The device operating conditions must not be exceeded in order to guarantee proper operation and reliability. The ranges in this table are design targets and actual data may vary in the given range.

NOTE

- For normal device operations, all supplies must be within operating range corresponding to the range mentioned in following tables. This is required even if some of the features are not used.
- If VDD_HV_A is in 3.3V range, VDD_HV_FLA should be externally supplied using a 3.3V source. If VDD_HV_A is in 3.3V range, VDD_HV_FLA should be shorted to VDD_HV_A.
- VDD_HV_A, VDD_HV_B and VDD_HV_C are all independent supplies and can each be set to 3.3V or 5V. The following tables: 'Recommended operating conditions (VDD_HV_x = 3.3 V)' and table 'Recommended operating conditions (VDD_HV_x = 5 V)' specify their ranges when configured in 3.3V or 5V respectively.

Table 6. Recommended operating conditions ($V_{DD\_HV\_x}$ = 3.3 V)

Symbol	Parameter	Conditions[1]	Min[2]	Max	Unit
$V_{DD\_HV\_A}$ $V_{DD\_HV\_B}$ $V_{DD\_HV\_C}$	HV IO supply voltage	—	3.15	3.6	V
$V_{DD\_HV\_FLA}$[3]	HV flash supply voltage	—	3.15	3.6	V
$V_{DD\_HV\_ADC1\_REF}$	HV ADC1 high reference voltage	—	3.0	5.5	V
$V_{DD\_HV\_ADC0}$ $V_{DD\_HV\_ADC1}$	HV ADC supply voltage	—	max(VDD_HV_A,VDD_HV_B,VDD_HV_C) - 0.05	3.6	V
$V_{SS\_HV\_ADC0}$ $V_{SS\_HV\_ADC1}$	HV ADC supply ground	—	-0.1	0.1	V
V_{DD_LV}[4, 5]	Core supply voltage	—	1.2	1.32	V
$V_{IN1\_CMP\_REF}$[6, 7]	Analog Comparator DAC reference voltage	—	3.15	3.6	V
I_{INJPAD}	Injected input current on any pin during overload condition	—	-3.0	3.0	mA

Table continues on the next page...

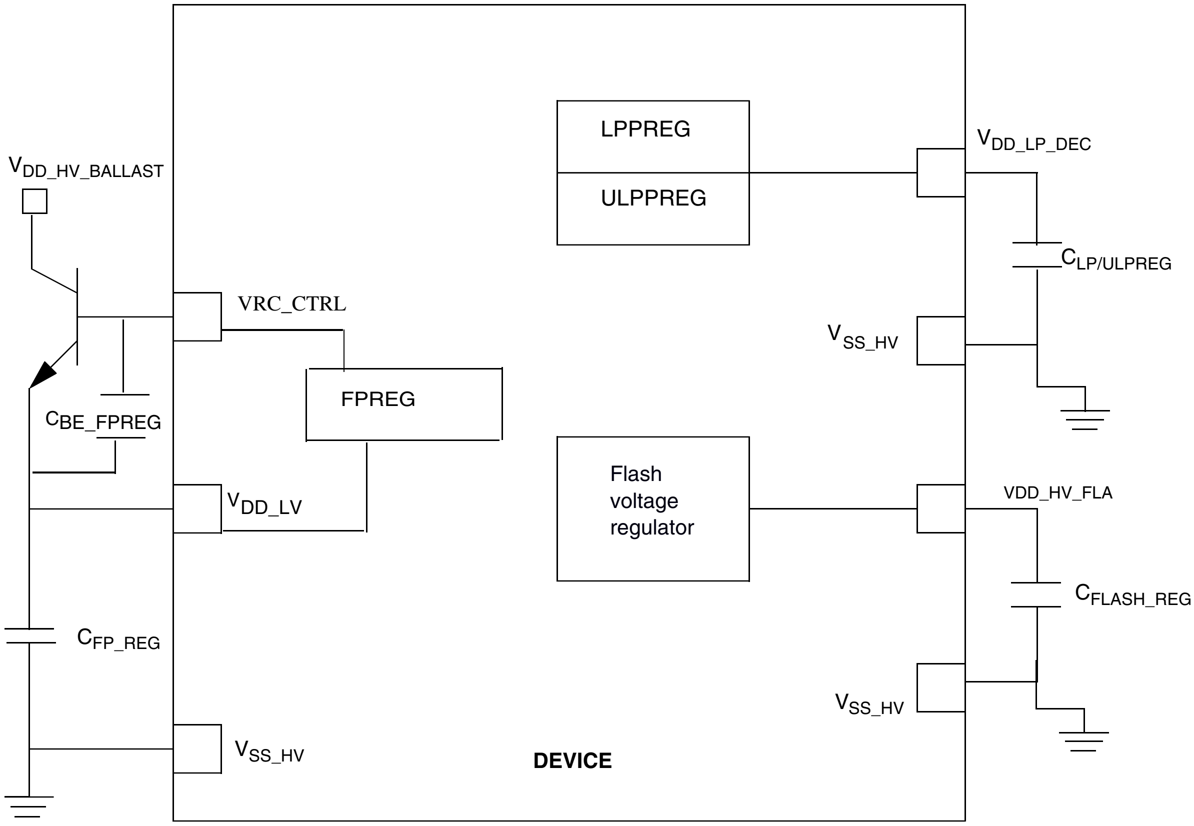

Figure 2. Voltage regulator capacitance connection

NOTE

On BGA, VSS_LV and VSS_HV have been joined on substrate and renamed as VSS.

Table 8. Voltage regulator electrical specifications

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
C_{fp_reg}[1]	External decoupling / stability capacitor	Min, max values shall be granted with respect to tolerance, voltage, temperature, and aging variations.	1.32	2.2[2]	3	µF
	Combined ESR of external capacitor	—	0.001	—	0.03	Ohm
C_{lp/ulp_reg}	External decoupling / stability capacitor for internal low power regulators	Min, max values shall be granted with respect to tolerance, voltage, temperature, and aging variations.	0.8	1	1.4	µF
	Combined ESR of external capacitor	—	0.001	—	0.1	Ohm
C_{be_fpreg}[3]	Capacitor in parallel to base-emitter	BCP68 and BCP56		3.3		nF
		MJD31		4.7		

Table continues on the next page...

5. 1. For VDD_HV_x, 1µf on each side of the chip
      a. 0.1 µf close to each VDD/VSS pin pair.
      b. 10 µf near for each power supply source
      c. For VDD_LV, 0.1uf close to each VDD/VSS pin pair is required. Depending on the the selected regulation mode, this amount of capacitance will need to be subtracted from the total capacitance required by the regulator for e.g., as specified by CFP_REG parameter.
   2. For VDD_LV, 0.1uf close to each VDD/VSS pin pair is required. Depending on the the selected regulation mode, this amount of capacitance will need to be subtracted from the total capacitance required by the regulator for e.g., as specified by CFP_REG parameter
6. Only applicable to ADC1
7. In external ballast configuration the following must be ensured during power-up and power-down (Note: If $V_{DD\_HV\_BALLAST}$ is supplied from the same source as VDD_HV_A this condition is implicitly met):
   - During power-up, $V_{DD\_HV\_BALLAST}$ must have met the min spec of 2.25V before VDD_HV_A reaches the POR_HV_RISE min of 2.75V.
   - During power-down, $V_{DD\_HV\_BALLAST}$ must not drop below the min spec of 2.25V until VDD_HV_A is below POR_HV_FALL min of 2.7V.

NOTE

For a typical configuration using an external ballast transistor with separate supply for VDD_HV_A and the ballast collector, a bulk storage capacitor (as defined in Table 8) is required on VDD_HV_A close to the device pins to ensure a stable supply voltage.

Extra care must be taken if the VDD_HV_A supply is also being used to power the external ballast transistor or the device is running in internal regulation mode. In these modes, the inrush current on device Power Up or on exit from Low Power Modes is significant and may case the VDD_HV_A voltage to drop resulting in an LVD reset event. To avoid this, the board layout should be optimized to reduce common trace resistance or additional capacitance at the ballast transistor collector (or VDD_HV_A pins in the case of internal regulation mode) is required. NXP recommends that customers simulate the external voltage supply circuitry.

In all circumstances, the voltage on VDD_HV_A must be maintained within the specified operating range (see Recommended operating conditions) to prevent LVD events.

Table 10. Current consumption characteristics (continued)

Symbol	Parameter	Conditions[1]	Min	Typ	Max	Unit
$I_{DD\_HV\_ADC\_REF}$[10, 11, 11]	ADC REF Operating current	T_a = 125 °C[5] 2 ADCs operating at 80 MHz $V_{DD\_HV\_ADC\_REF}$ = 5.5 V	—	200	400	µA
		T_a = 105 °C 2 ADCs operating at 80 MHz $V_{DD\_HV\_ADC\_REF}$ = 5.5 V	—	200	—	
		T_a = 85 °C 2 ADCs operating at 80 MHz $V_{DD\_HV\_ADC\_REF}$ = 5.5 V	—	200	—	
		T_a = 25 °C 2 ADCs operating at 80 MHz $V_{DD\_HV\_ADC\_REF}$ = 3.6 V	—	200	—	
$I_{DD\_HV\_ADCx}$[11]	ADC HV Operating current	T_a = 125 °C[5] ADC operating at 80 MHz $V_{DD\_HV\_ADC}$ = 5.5 V	—	1.2	2	mA
		T_a = 25 °C ADC operating at 80 MHz $V_{DD\_HV\_ADC}$ = 3.6 V	—	1	2	
$I_{DD\_HV\_FLASH}$[12]	Flash Operating current during read access	T_a = 125 °C[5] 3.3 V supplies 160 MHz frequency	—	40	45	mA
		T_a = 105 °C 3.3 V supplies 160 MHz frequency	—	40	45	
		T_a = 85 °C 3.3 V supplies 160 MHz frequency	—	40	45	

1. The content of the Conditions column identifies the components that draw the specific current.
2. Single e200Z4 core cache disabled @80 MHz, no FlexRay, no ENET, 2 x CAN, 8 LINFlexD, 2 SPI, ADC0 and 1 used constantly, no HSM, Memory: 2M flash, 128K RAM RUN mode, Clocks: FIRC on, XOSC, PLL on, SIRC on for TOD, no 32KHz crystal (TOD runs off SIRC).
3. Recommended Transistors:MJD31 @ 85°C, 105°C and 125°C. In case of internal ballast mode, it is expected that the external ballast is not mounted and BAL_SELECT_INT pin is tied to VDD_HV_A supply on board. Internal ballast can be used for all use cases with current consumption upto 150mA
4. The power consumption does not consider the dynamic current of I/Os
5. Tj=150°C. Assumes Ta=125°C
   - Assumes maximum θJA of 2s2p board. SeeThermal attributes
6. e200Z4 core, 160MHz, cache enabled; e200Z2 core , 80MHz, no FlexRay, no ENET, 7 CAN, 16 LINFlexD, 4 SPI, 1x ADC used constantly, includes HSM at start-up / periodic use, Memory: 3M flash, 256K RAM, Clocks: FIRC on, XOSC on, PLL on, SIRC on, no 32KHz crystal
7. e200Z4 core, 120MHz, cache enabled; e200Z2 core, 60MHz; no FlexRay, no ENET, 7 CAN, 16 LINFlexD, 4 SPI, 1x ADC used constantly, includes HSM at start-up / periodic use, Memory: 3M flash, 128K RAM, Clocks: FIRC on, XOSC on, PLL on, SIRC on, no 32KHz crystal

4.7 Electromagnetic Compatibility (EMC) specifications

EMC measurements to IC-level IEC standards are available from NXP on request.

5 I/O parameters

5.1 AC specifications @ 3.3 V Range

Table 14. Functional Pad AC Specifications @ 3.3 V Range

Symbol	Prop. Delay (ns)[1] L>H/H>L		Rise/Fall Edge (ns)		Drive Load (pF)	SIUL2_MSCRn[SRC 1:0]
	Min	Max	Min	Max		MSB,LSB
pad_sr_hv (output)		6/6		1.9/1.5	25	11
	2.5/2.5	8.25/7.5	0.8/0.6	3.25/3	50	
	6.4/5	19.5/19.5	3.5/2.5	12/12	200	
	2.2/2.5	8/8	0.55/0.5	3.9/3.5	25	10
	0.090	1.1	0.035	1.1	asymmetry[2]	
	2.9/3.5	12.5/11	1/1	7/6	50	
	11/8	35/31	7.7/5	25/21	200	
	8.3/9.6	45/45	4/3.5	25/25	50	01[3]
	13.5/15	65/65	6.3/6.2	30/30	200	
	13/13	75/75	6.8/6	40/40	50	00[3]
	21/22	100/100	11/11	51/51	200	
pad_i_hv/ pad_sr_hv (input)[4]		2/2		0.5/0.5	0.5	NA

1. As measured from 50% of core side input to Voh/Vol of the output
2. This row specifies the min and max asymmetry between both the prop delay and the edge rates for a given PVT and 25pF load. Required for the Flexray spec.
3. Slew rate control modes
4. Input slope = 2ns

NOTE

The specification given above is based on simulation data into an ideal lumped capacitor. Customer should use IBIS models for their specific board/loading conditions to simulate the expected signal integrity and edge rates of their system.

NOTE

The specification given above is measured between 20% / 80%.

5.2 DC electrical specifications @ 3.3V Range

Table 15. DC electrical specifications @ 3.3V Range

Symbol	Parameter	Value		Unit
		Min	Max	
Vih (pad_i_hv)	Pad_I_HV Input Buffer High Voltage	0.72*VDD_HV_x	VDD_HV_x + 0.3	V
Vil (pad_i_hv)	Pad_I_HV Input Buffer Low Voltage	VDD_HV_x - 0.3	0.45*VDD_HV_x	V
Vhys (pad_i_hv)	Pad_I_HV Input Buffer Hysteresis	0.11*VDD_HV_x		V
Vih_hys	CMOS Input Buffer High Voltage (with hysteresis enabled)	0.67*VDD_HV_x	VDD_HV_x + 0.3	V
Vil_hys	CMOS Input Buffer Low Voltage (with hysteresis enabled)	VDD_HV_x - 0.3	0.35*VDD_HV_x	V
Vih	CMOS Input Buffer High Voltage (with hysteresis disabled)	0.57 * VDD_HV_x[1, 1]	VDD_HV_x[1] + 0.3	V
Vil	CMOS Input Buffer Low Voltage (with hysteresis disabled)	VDD_HV_x - 0.3	0.4 * VDD_HV_x[1]	V
Vhys	CMOS Input Buffer Hysteresis	0.09 * VDD_HV_x[1]		V
Pull_IIH (pad_i_hv)	Weak Pullup Current[2, 2] Low	15		µA
Pull_IIH (pad_i_hv)	Weak Pullup Current[3, 3] High		55	µA
Pull_IIL (pad_i_hv)	Weak Pulldown Current[3] Low	28		µA
Pull_IIL (pad_i_hv)	Weak Pulldown Current[2] High		85	µA
Pull_Ioh	Weak Pullup Current[4]	15	50	µA
Pull_Iol	Weak Pulldown Current[5]	15	50	µA
Iinact_d	Digital Pad Input Leakage Current (weak pull inactive)	-2.5	2.5	µA
Voh	Output High Voltage[6]	0.8 *VDD_HV_x[1]	—	V
Vol	Output Low Voltage[7] Output Low Voltage[8]	—	0.2 *VDD_HV_x[1] 0.1 *VDD_HV_x	V
Ioh_f	Full drive Ioh[9, 9] (SIUL2_MSCRn.SRC[1:0] = 11)	18	70	mA
Iol_f	Full drive Iol[9] (SIUL2_MSCRn.SRC[1:0] = 11)	21	120	mA
Ioh_h	Half drive Ioh[9] (SIUL2_MSCRn.SRC[1:0] = 10)	9	35	mA
Iol_h	Half drive Iol[9] (SIUL2_MSCRn.SRC[1:0] = 10)	10.5	60	mA

1. VDD_HV_x = VDD_HV_A, VDD_HV_B, VDD_HV_C
2. Measured when pad=0.69*VDD_HV_x
3. Measured when pad=0.49*VDD_HV_x
4. Measured when pad = 0 V
5. Measured when pad = VDD_HV_x
6. Measured when pad is sourcing 2 mA
7. Measured when pad is sinking 2 mA
8. Measured when pad is sinking 1.5 mA
9. Ioh/Iol is derived from spice simulations. These values are NOT guaranteed by test.

Table 21. ADC conversion characteristics (for 10-bit) (continued)

Symbol	Parameter	Conditions	Min	Typ[1]	Max	Unit
t_{conv}	Conversion time[4]	80 MHz	550	—	—	ns
t_{total_conv}	Total Conversion time tsample + tconv (for standard channels)	80 MHz	1	—	—	μs
	Total Conversion time tsample + tconv (for extended channels)		1.5	—	—	
C_S[5]	ADC input sampling capacitance	—	—	3	5	pF
C_{P1}[5]	ADC input pin capacitance 1	—	—	—	5	pF
C_{P2}[5]	ADC input pin capacitance 2	—	—	—	0.8	pF
R_{SW1}[5]	Internal resistance of analog source	V_{REF} range = 4.5 to 5.5 V	—	—	0.3	kΩ
		V_{REF} range = 3.15 to 3.6 V	—	—	875	Ω
R_{AD}[5]	Internal resistance of analog source	—	—	—	825	Ω
INL	Integral non-linearity	—	–2	—	2	LSB
DNL	Differential non-linearity	—	–1	—	1	LSB
OFS	Offset error	—	–4	—	4	LSB
GNE	Gain error	—	–4	—	4	LSB
ADC Analog Pad (pad going to one ADC)	Max leakage (standard channel)	150 °C	—	—	2500	nA
	Max positive/negative injection		–5	—	5	mA
	Max leakage (standard channel)	105 °C $_{TA}$	—	5	250	nA
$TUE_{standard/extended\ channels}$	Total unadjusted error for standard channels	Without current injection	–4	+/-3	4	LSB
		With current injection[6]		+/-4		LSB
$t_{recovery}$	STOP mode to Run mode recovery time				< 1	μs

1. Active ADC Input, VinA < [min(ADC_ADV, IO_Supply_A,B,C)]. Violation of this condition would lead to degradation of ADC performance. Please refer to Table: 'Absolute maximum ratings' to avoid damage. Refer to Table: 'Recommended operating conditions' for required relation between IO_supply_A, B, C and ADC_Supply.
2. The internally generated clock (known as AD_clk or ADCK) could be same as the peripheral clock or half of the peripheral clock based on register configuration in the ADC.
3. During the sample time the input capacitance C_S can be charged/discharged by the external source. The internal resistance of the analog source must allow the capacitance to reach its final voltage level within t_{sample}. After the end of the sample time t_{sample}, changes of the analog input voltage have no effect on the conversion result. Values for the sample clock t_{sample} depend on programming.
4. This parameter does not include the sample time t_{sample}, but only the time for determining the digital result and the time to load the result register with the conversion result.
5. See Figure 65
6. Current injection condition for ADC channels is defined for an inactive ADC channel (on which conversion is NOT being performed), and this occurs when voltage on the ADC pin exceeds the I/O supply or ground. However, absolute maximum voltage spec on pad input (VINA, see Table: Absolute maximum ratings) must be honored to meet TUE spec quoted here

6.2 Clocks and PLL interfaces modules

6.2.1 Main oscillator electrical characteristics

This device provides a driver for oscillator in pierce configuration with amplitude control. Controlling the amplitude allows a more sinusoidal oscillation, reducing in this way the EMI. Other benefits arises by reducing the power consumption. This Loop Controlled Pierce (LCP mode) requires good practices to reduce the stray capacitance of traces between crystal and MCU.

An operation in Full Swing Pierce (FSP mode), implemented by an inverter is also available in case of parasitic capacitances and cannot be reduced by using crystal with high equivalent series resistance. For this mode, a special care needs to be taken regarding the serial resistance used to avoid the crystal overdrive.

Other two modes called External (EXT Wave) and disable (OFF mode) are provided. For EXT Wave, the drive is disabled and an external source of clock within CMOS level based in analog oscillator supply can be used. When OFF, EXTAL is pulled down by 240 Kohms resistor and the feedback resistor remains active connecting XTAL through EXTAL by 1M resistor.

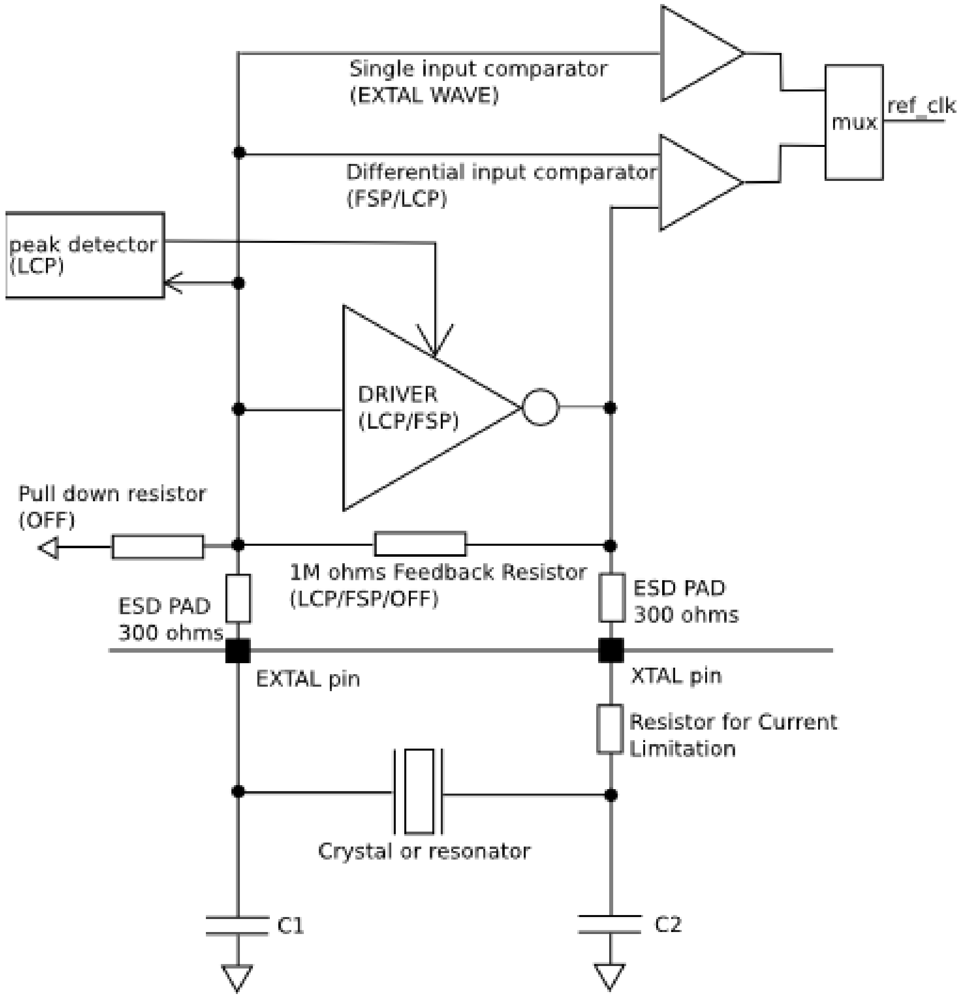

Figure 7. Oscillator connections scheme

Table 23. Main oscillator electrical characteristics

Symbol	Parameter	Mode	Conditions	Min	Typ	Max	Unit
f_{XOSCHS}	Oscillator frequency	FSP/LCP		8		40	MHz
$g_{mXOSCHS}$	Driver Transconductance	LCP			23		mA/V
		FSP			33		
V_{XOSCHS}	Oscillation Amplitude	LCP[1, 2, 1, 2]	8 MHz		1.0		V_{PP}
			16 MHz		1.0		
			40 MHz		0.8		
$T_{XOSCHSSU}$	Startup time	FSP/LCP[1]	8 MHz		2		ms
			16 MHz		1		
			40 MHz		0.5		

Table continues on the next page...

Table 23. Main oscillator electrical characteristics (continued)

Symbol	Parameter	Mode	Conditions	Min	Typ	Max	Unit
	Oscillator Analog Circuit supply current	FSP	8 MHz		2.2		mA
			16 MHz		2.2		
			40 MHz		3.2		
		LCP	8 MHz		141		uA
			16 MHz		252		
			40 MHz		518		
V_{IH}	Input High level CMOS Schmitt trigger	EXT Wave	Oscillator supply=3.3	1.95			V
V_{IL}	Input low level CMOS Schmitt trigger	EXT Wave	Oscillator supply=3.3			1.25	V

1. Values are very dependent on crystal or resonator used and parasitic capacitance observed in the board.
2. Typ value for oscillator supply 3.3 V@27 °C

6.2.2 32 kHz Oscillator electrical specifications

Table 24. 32 kHz oscillator electrical specifications

Symbol	Parameter	Condition	Min	Typ	Max	Unit
f_{osc_lo}	Oscillator crystal or resonator frequency		32		40	KHz
t_{cst}	Crystal Start-up Time[1, 2]				2	s

1. This parameter is characterized before qualification rather than 100% tested.
2. Proper PC board layout procedures must be followed to achieve specifications.

6.2.3 16 MHz RC Oscillator electrical specifications

Table 25. 16 MHz RC Oscillator electrical specifications

Symbol	Parameter	Conditions	Value			Unit
			Min	Typ	Max	
F_{Target}	IRC target frequency	—	—	16	—	MHz
PTA	IRC frequency variation after trimming	—	-5	—	5	%
$T_{startup}$	Startup time	—		—	1.5	us
T_{STJIT}	Cycle to cycle jitter		—	—	1.5	%
T_{LTJIT}	Long term jitter		—	—	0.2	%

NOTE

The above start up time of 1 us is equivalent to 16 cycles of 16 MHz.

6.2.4 128 KHz Internal RC oscillator Electrical specifications

Table 26. 128 KHz Internal RC oscillator electrical specifications

Symbol	Parameter	Condition	Min	Typ	Max	Unit
F_{oscu}[1]	Oscillator frequency	Calibrated	119	128	136.5	KHz
	Temperature dependence				600	ppm/C
	Supply dependence				18	%/V
	Supply current	Clock running			2.75	µA
		Clock stopped			200	nA

1. Vdd=1.2 V, 1.32V, T_a=-40 C, 125 C

6.2.5 PLL electrical specifications

Table 27. PLL electrical specifications

Parameter	Min	Typ	Max	Unit	Comments
Input Frequency	8		40	MHz	
VCO Frequency Range	600		1280	MHz	
Duty Cycle at pllclkout	48%		52%		This specification is guaranteed at PLL IP boundary
Period Jitter			See Table 28	ps	NON SSCG mode
TIE			See Table 28		at 960 M Integrated over 1MHz offset not valid in SSCG mode
Modulation Depth (Center Spread)	+/- 0.25%		+/- 3.0%		
Modulation Frequency			32	KHz	
Lock Time			60	µs	Calibration mode

Table 28. Jitter calculation

Type of jitter	Jitter due to Supply Noise (ps) J_{SN}[1]	Jitter due to Fractional Mode (ps) J_{SDM}[2]	Jitter due to Fractional Mode J_{SSCG} (ps) [3]	1 Sigma Random Jitter J_{RJ} (ps) [4]	Total Period Jitter (ps)
Period Jitter	60 ps	3% of pllclkout1,2	Modulation depth	0.1% of pllclkout1,2	$+/-(J_{SN}+J_{SDM}+J_{SSCG}+N^{[4]}\times J_{RJ})$

Table continues on the next page...

Table 30. Flash memory program and erase specifications

Symbol	Characteristic[1]	Typ[2]	Factory Programming[3, 4]		Field Update			Unit
			Initial Max	Initial Max, Full Temp	Typical End of Life[5]	Lifetime Max[6]		
			20°C ≤T_A ≤30°C	-40°C ≤T_J ≤150°C	-40°C ≤T_J ≤150°C	≤ 1,000 cycles	≤ 250,000 cycles	
t_{dwpgm}	Doubleword (64 bits) program time	43	100	150	55	500		μs
t_{ppgm}	Page (256 bits) program time	73	200	300	108	500		μs
t_{qppgm}	Quad-page (1024 bits) program time	268	800	1,200	396	2,000		μs
t_{16kers}	16 KB Block erase time	168	290	320	250	1,000		ms
t_{16kpgm}	16 KB Block program time	34	45	50	40	1,000		ms
t_{32kers}	32 KB Block erase time	217	360	390	310	1,200		ms
t_{32kpgm}	32 KB Block program time	69	100	110	90	1,200		ms
t_{64kers}	64 KB Block erase time	315	490	590	420	1,600		ms
t_{64kpgm}	64 KB Block program time	138	180	210	170	1,600		ms
$t_{256kers}$	256 KB Block erase time	884	1,520	2,030	1,080	4,000	—	ms
$t_{256kpgm}$	256 KB Block program time	552	720	880	650	4,000	—	ms

1. Program times are actual hardware programming times and do not include software overhead. Block program times assume quad-page programming.
2. Typical program and erase times represent the median performance and assume nominal supply values and operation at 25 °C. Typical program and erase times may be used for throughput calculations.
3. Conditions: ≤ 150 cycles, nominal voltage.
4. Plant Programing times provide guidance for timeout limits used in the factory.
5. Typical End of Life program and erase times represent the median performance and assume nominal supply values. Typical End of Life program and erase values may be used for throughput calculations.
6. Conditions: -40°C ≤ T_J ≤ 150°C, full spec voltage.

6.3.2 Flash memory Array Integrity and Margin Read specifications

Table 31. Flash memory Array Integrity and Margin Read specifications

Symbol	Characteristic	Min	Typical	Max[1, 1]	Units[2, 2]
$t_{ai16kseq}$	Array Integrity time for sequential sequence on 16 KB block.	—	—	512 x Tperiod x Nread	—
$t_{ai32kseq}$	Array Integrity time for sequential sequence on 32 KB block.	—	—	1024 x Tperiod x Nread	—
$t_{ai64kseq}$	Array Integrity time for sequential sequence on 64 KB block.	—	—	2048 x Tperiod x Nread	—

Table continues on the next page...

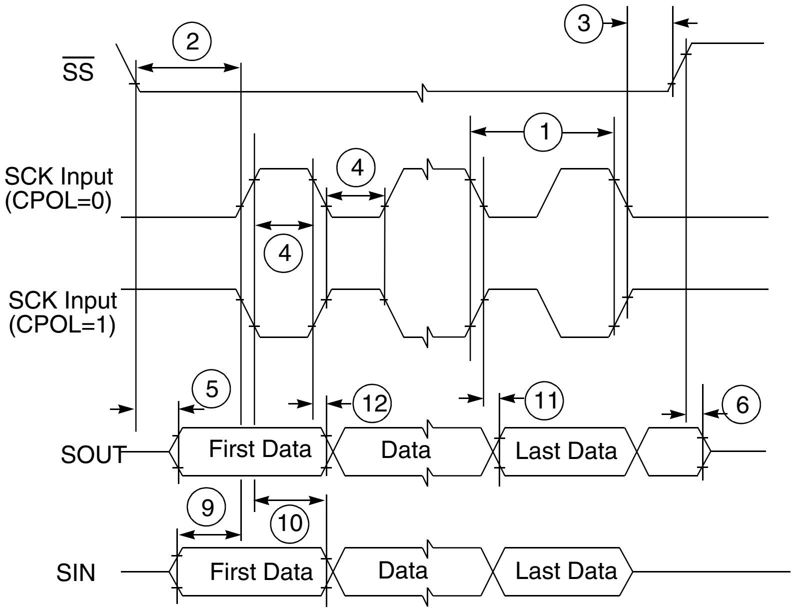

Figure 10. DSPI classic SPI timing — slave, CPHA = 0

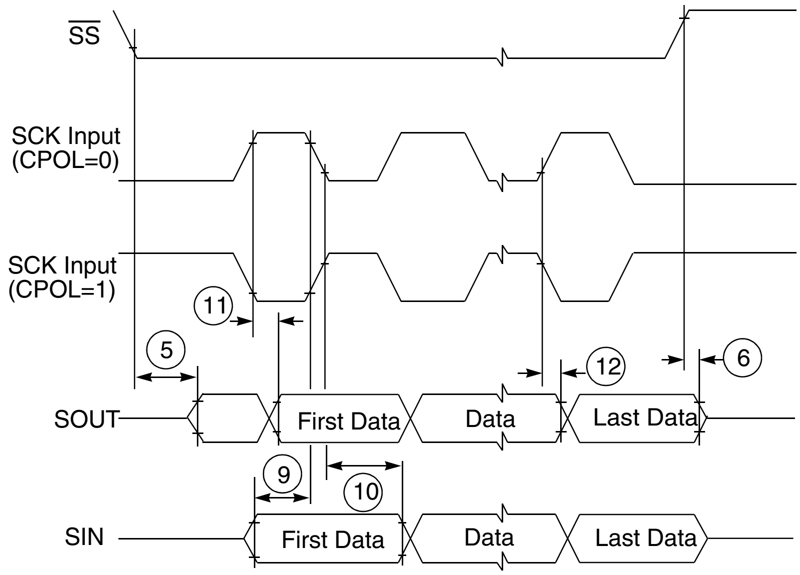

Figure 11. DSPI classic SPI timing — slave, CPHA = 1

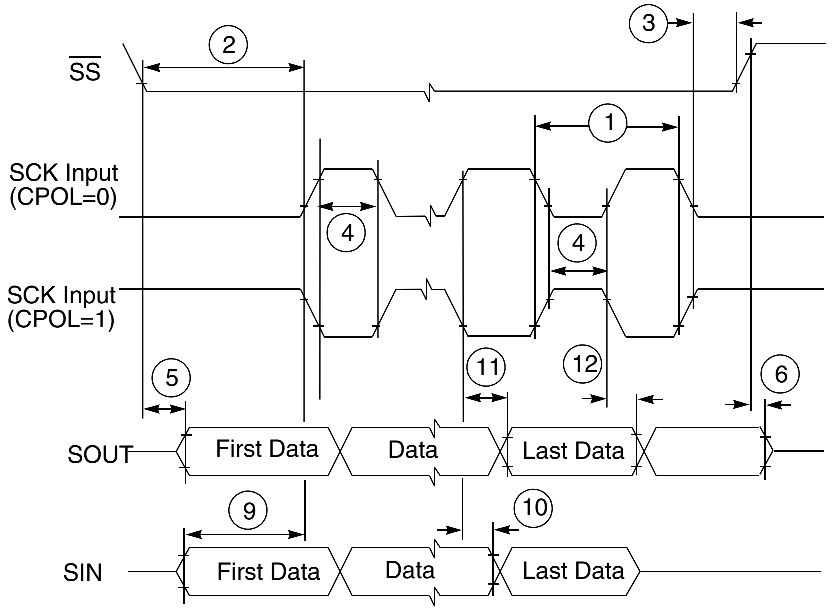

Figure 14. DSPI modified transfer format timing – slave, CPHA = 0

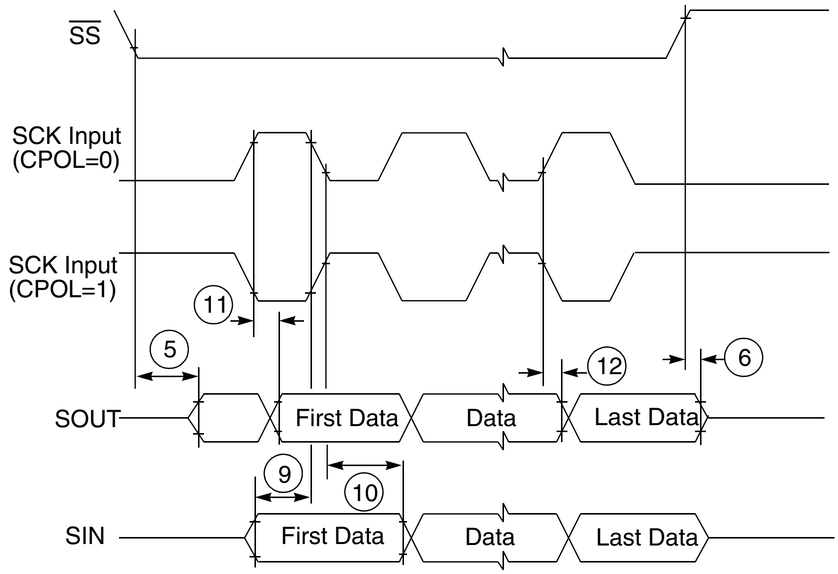

Figure 15. DSPI modified transfer format timing — slave, CPHA = 1

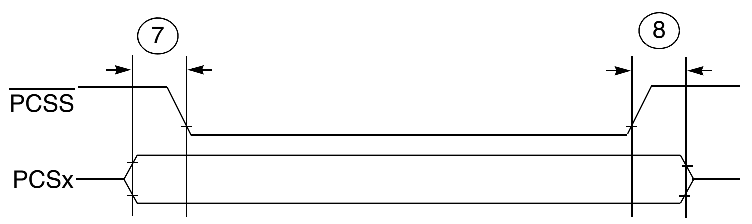

Figure 16. DSPI PCS strobe (PCSS) timing

Table 43. Master mode SAI Timing (continued)

no	Parameter	Value		Unit
		Min	Max	
S2	SAI_MCLK pulse width high/low	45%	55%	MCLK period
S3	SAI_BCLK cycle time	80	-	BCLK period
S4	SAI_BCLK pulse width high/low	45%	55%	ns
S5	SAI_BCLK to SAI_FS output valid	-	15	ns
S6	SAI_BCLK to SAI_FS output invalid	0	-	ns
S7	SAI_BCLK to SAI_TXD valid	-	15	ns
S8	SAI_BCLK to SAI_TXD invalid	0	-	ns
S9	SAI_RXD/SAI_FS input setup before SAI_BCLK	28	-	ns
S10	SAI_RXD/SAI_FS input hold after SAI_BCLK	0	-	ns

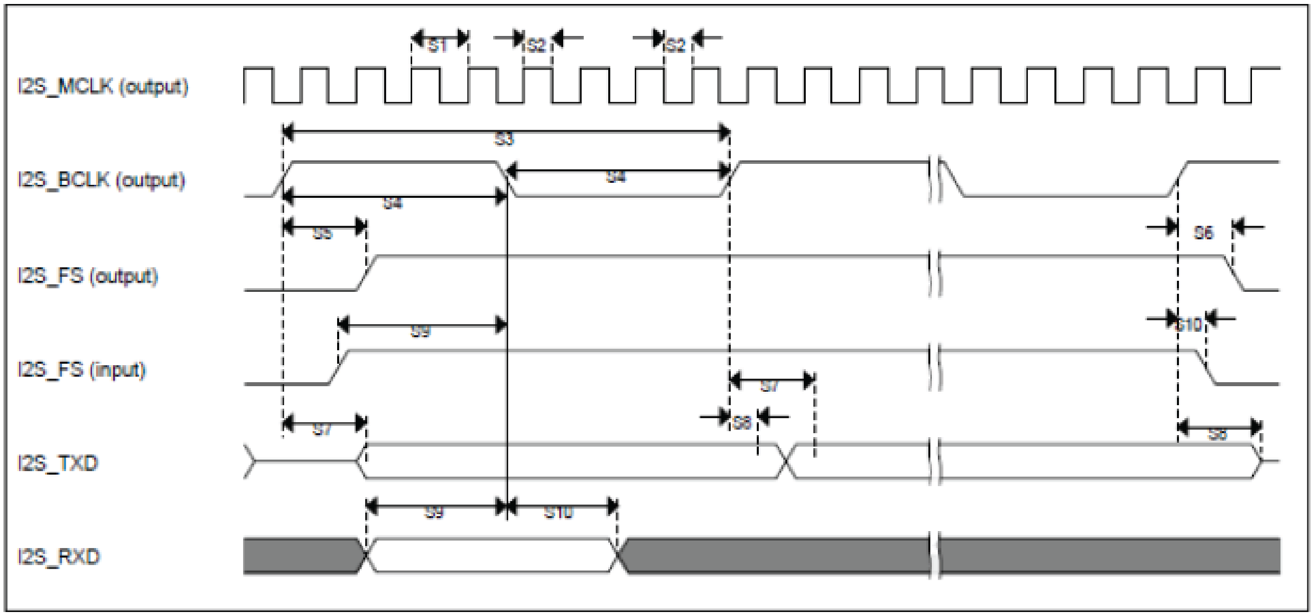

Figure 23. Master mode SAI Timing

Table 44. Slave mode SAI Timing

No	Parameter	Value		Unit
		Min	Max	
	Operating Voltage	2.7	3.6	V
S11	SAI_BCLK cycle time (input)	80	-	ns
S12	SAI_BCLK pulse width high/low (input)	45%	55%	BCLK period
S13	SAI_FS input setup before SAI_BCLK	10	-	ns
S14	SAI_FS input hold after SAI_BCLK	2	-	ns

Table continues on the next page...

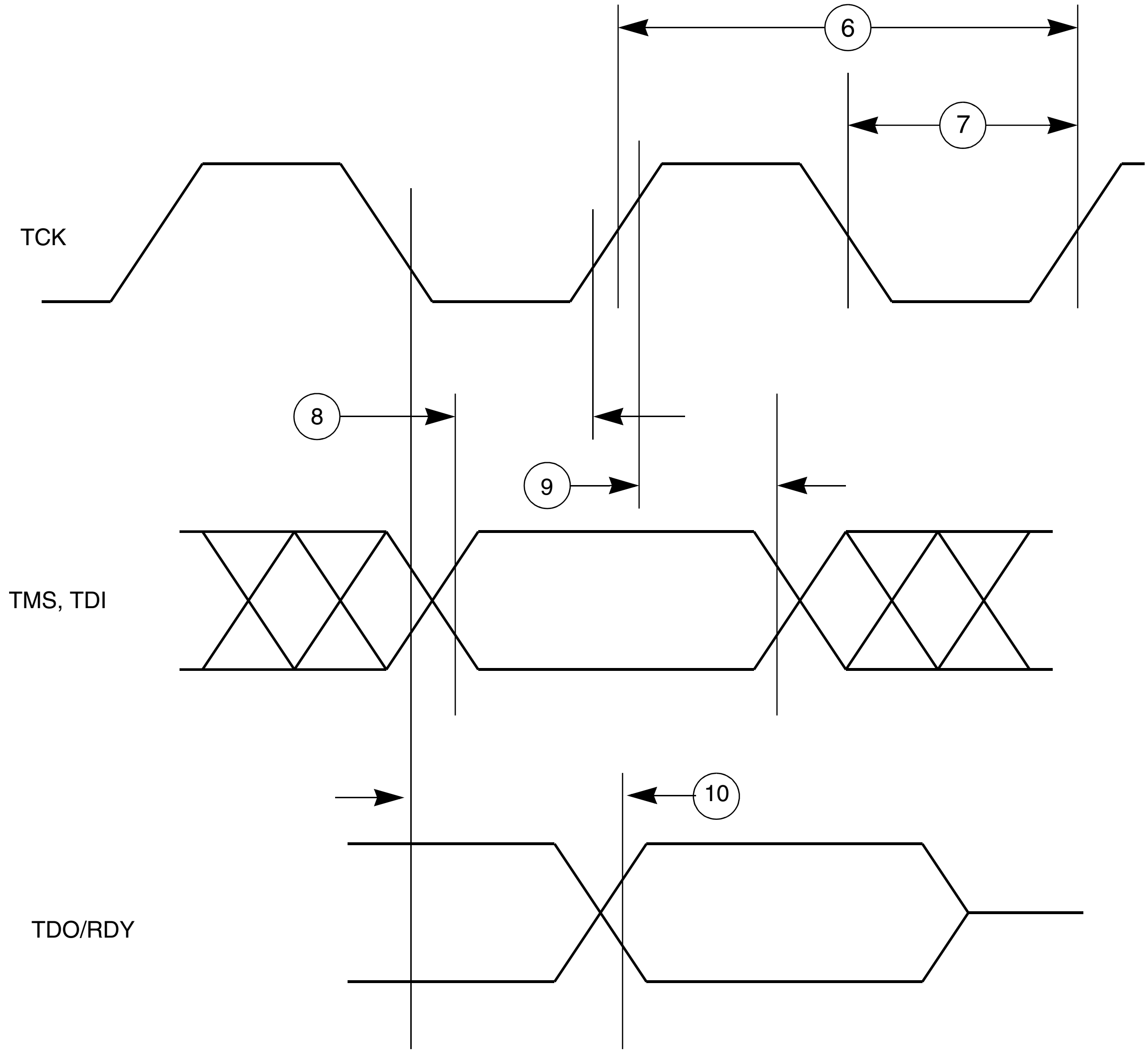

Figure 30. Nexus TDI, TMS, TDO timing

6.5.3 WKPU/NMI timing

Table 47. WKPU/NMI glitch filter

No.	Symbol	Parameter	Min	Typ	Max	Unit
1	W_{FNMI}	NMI pulse width that is rejected	—	—	20	ns
2	$W_{NFNMI}D$	NMI pulse width that is passed	400	—	—	ns

Package	NXP Document Number
176-pin LQFP-EP	98ASA00698D
256 MAPBGA	98ASA00346D
324 MAPBGA	98ASA10582D

9 Pinouts

9.1 Package pinouts and signal descriptions

For package pinouts and signal descriptions, refer to the Reference Manual.

10 Reset sequence

10.1 Reset sequence

This section describes different reset sequences and details the duration for which the device remains in reset condition in each of those conditions.

10.1.1 Reset sequence duration

Table 49 specifies the reset sequence duration for the five different reset sequences described in Reset sequence description.

Table 49. RESET sequences

No.	Symbol	Parameter	T_{Reset}			Unit
			Min	Typ [1, 1]	Max	
1	T_{DRB}	Destructive Reset Sequence, BIST enabled	6.2	7.3	-	ms
2	T_{DR}	Destructive Reset Sequence, BIST disabled	110	182	-	us
3	T_{ERLB}	External Reset Sequence Long, Unsecure Boot	6.2	7.3	-	ms
4	T_{FRL}	Functional Reset Sequence Long, Unsecure Boot	110	182	-	us
5	T_{FRS}	Functional Reset Sequence Short, Unsecure Boot	7	9	-	us

1. The Typ value is applicable only if the reset sequence duration is not prolonged by an extended assertion of RESET_B by an external reset generator.

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